

TEM-F-780/1-50mW



INFRARED DIODE LASER AT 780nm

It features TEM₀₀ mode, ultra compact design, long lifetime, cost-effectiveness and easy operation. They are used in measurement, communication, spectrum analysis, etc.



SPECIFICATIONS

Central wavelength (nm)	780±10
Operating mode	CW
Output power (mW) ¹	1-50
Power stability (rms, 4 hours ± 3°C)	<2%, <1%, <0.5%
Transverse mode	TEM ₀₀
Ellipticity	>0.95
M ²	<1.1
Beam diameter at the aperture (1/e ² , mm)	~1.0
Beam divergence, full angle (mrad)	<1.5
Warm-up time (minutes)	<5
Beam height from base plate (mm)	25
Operating temperature (°C)	25±3
Power supply (100-240VAC)	PSU-III-FDA/PSU-III-LED/PSU-A-D
Modulation option	DC-1kHz, 1kHz-10kHz, 10kHz-30kHz, 30kHz-100kHz optional; TTL and Analog optional
Expected lifetime (hours)	>10000



LASER HEAD²



146 (L) × 58 (W) × 45 (H) mm³, 0.7kg

HEATSINK (TC-06) optional



220 (L) × 100 (W) × 51 (H) mm³, 0.6kg

POWER SUPPLY (PSU-III-FDA) ³	POWER SUPPLY (PSU-III-LED) ⁴	POWER SUPPLY (PSU-A-D) ⁵
 171 (L) × 130 (W) × 62.2 (H) mm³, 1.2kg	 179 (L) × 155 (W) × 92 (H) mm³, 1.5kg	 162 (L) × 144 (W) × 70 (H) mm³, 1.0kg

1 Any power level can be selected in this range.

2 The laser head needs to be used on a heat sink with good heat dissipation.

3 Fixed output power; Modulation up to 30kHz.

4 Output power adjustable 10-100%; RS232 control optional; Modulation up to 30kHz.

5 Output power adjustable 10-100%; RS232 control optional; Modulation up to 100kHz.